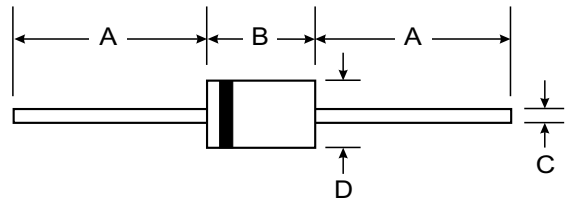
1N5711/1N6263

15mA Axial Leaded Schottky Barrier Diodes

Features

- For general purpose applications
- Metal-on-silicon Schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications.
- This diode is also available in the MiniMELF case with type designation LL5711 and LL6263.
- Pb / RoHS Free



DO-35		
Dim	**Min**	**Max**
A	25.40	—
B	—	4.00
C	—	0.60
D	—	2.00
All Dimensions in mm		

Mechanical Data

- **Case:** DO-35 Glass Case
- **Weight:** approx. 0.13g

Maximum Ratings and Electrical Characteristics

@ T_A = 25°C unless otherwise specified

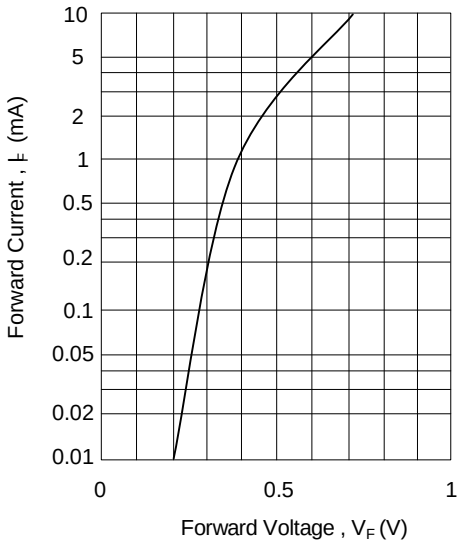
Parameter		**Symbol**	**Value**	**Unit**
Repetitive Peak Reverse Voltage	1N5711	V_{RRM}	70	V
	1N6263		60	
Power Dissipation (Infinite Heatsink)		P_D	400(1)	mW
Maximum Single Cycle Surge 10 μs Square Wave		I_{FSM}	2	A
Thermal Resistance Junction to Ambient Air		$R_{\theta JA}$	0.3(1)	°C/mW
Junction Temperature		T_J	125(1)	°C
Storage temperature range		T_S	-55 to + 150 (1)	°C

Parameter		**Symbol**	**Test Condition**	**Min**	**Typ**	**Max**	**Unit**
Reverse Breakdown Voltage	1N5711	$V_{(BR)R}$	I_R = 10 μA	70	-	-	V
	1N6263			60	-	-	
Reverse Current		I_R	V_R = 50 V	-	-	200	nA
Forward Voltage Drop		V_F	I_F = 1mA	-	-	0.41	V
			I_F = 15mA	-	-	1.0	
Diode Capacitance	1N5711	Cd	V_R = 0 V, f = 1MHz	-	-	2.0	pF
	1N6263			-	-	2.2	
Reverse Recovery Time		Trr	$I_F = I_R$ = 5mA, recover to 0.1I_R	-	-	1	ns

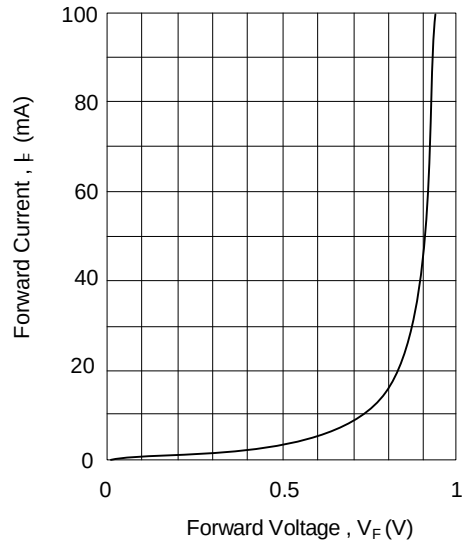
Note:

(1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature..

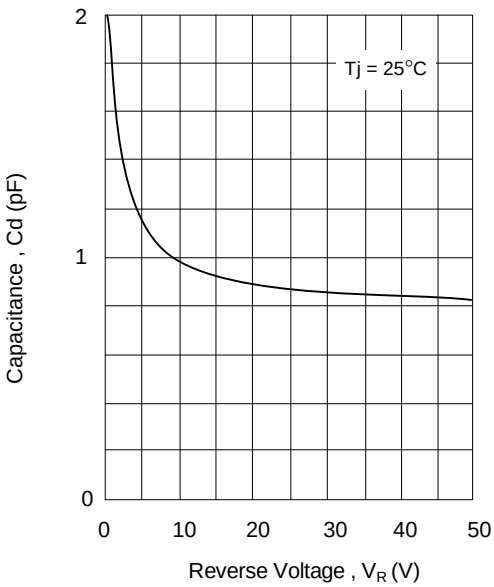
Typical variation of forward current and forward voltage for primary conduction through the schottky barrier



Typical forward conduction curve of combination schottky barrier and PN junction guard ring



Typical capacitance curve as a function of reverse voltage



Typical variation of reverse current at various temperatures